

Q3 3. (Amended) A polycrystalline silicon film, the polycrystalline film containing Ni atoms of which density ranges 2×10^{17} to 5×10^{19} atoms/cm³, and an electrical conductivity activation energy between 0.52eV and 0.71eV, the polycrystalline silicon film comprising a plurality of needle-shaped silicon crystallites, the polycrystalline silicon film on an insulating substrate.

Q4 6. (Amended) A polycrystalline silicon film, the polycrystalline film containing metal of which density ranges 2×10^{17} to 5×10^{19} atoms/cm³, and an electrical conductivity activation energy between 0.52eV and 0.71eV, the polycrystalline silicon film comprising a plurality of needle-shaped silicon crystallites wherein the metal is a catalyst for metal induced crystallization of silicon.

Q5 9. (Amended) A polycrystalline silicon film, the polycrystalline film containing metal of which density ranges 2×10^{17} to 5×10^{19} atoms/cm³, and an electrical conductivity activation energy between 0.52eV and 0.71eV, the polycrystalline silicon film comprising a plurality of needle-shaped silicon crystallites wherein the metal is a catalyst for metal induced crystallization of amorphous silicon.

REMARKS

In the Office Action dated May 21, 2001, the Examiner rejected claims 1-9 under 35 U.S.C. § 112, second paragraph, and rejected claims 1-9 under 35 U.S.C. § 102(b) as being anticipated by Ohtani et al.

By this Amendment, Applicant cancels claim 8 without prejudice or disclaimer and amends claims 1, 3, 6 and 9. Accordingly, claims 1-7, and 9 are pending in this application.

The Examiner rejected claims 1-9 under 35 U.S.C. § 112, second paragraph, as being indefinite and unclear as to the scope of "bar-like" crystallite as it pertains to Figs. 11B, 11C,